

IN THE SPECIFICATION

Page 4, line 21, after "weak.", please start an new line and insert the following new paragraph.

Typically the P-channel transistor used as an ideal key and the N-channel transistor are of the CMOS type. Also, typically the N-channel transistor is able to represent an active load. Also, typically the number of N-type transistors is variable from 1 to 12, in order to increase by a corresponding value the logarithmic conversion gain of said current photo-generated by said photo-sensitive reception means.

Page 8, line 30, after "fourth.", please start an new line and insert the following new paragraph.

Typically the first and second transistors 21, 22 are of the CMOS type. When the first transistor 21 is of the P-channel type, it is able to represent an ideal key, and when the second transistor 22 is of the N-channel type it is able to represent an active load. Typically, the number of N-type transistors is variable from 1 to 12, in order to increase by a corresponding value the logarithmic conversion gain of the current photo-generated by the photo-sensitive reception means 11.

Page 9, line 33, please amend the paragraph starting on this line as follows.

During the integration phase the signal 27 is taken to a high tension so that the first transistor 21 enters ~~a~~ an interdiction zone.